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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/845,231	04/30/2001	Arvind Halliyal	F0630	3855
7:	590 06/22/2005		EXAMINER	
Himanshu S. Amin		BARAN, MARY C		
Amin & Turocy, LLP National City Center, 24th Floor		ART UNIT	PAPER NUMBER	
1900 E. 9th Street Cleveland, OH 44114			2857	
		DATE MAILED: 06/22/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

				$A \cdot H$		
		Application No.	Applicant(s)	-,( )		
		09/845,231	HALLIYAL ET AL.			
	Office Action Summary	Examiner	Art Unit			
		Mary Kate B. Baran	2857			
Period fo	The MAILING DATE of this communication app or Reply	pears on the cover sheet with the	correspondence address			
THE - External after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. msions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period vere to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be t y within the statutory minimum of thirty (30) da will apply and will expire SIX (6) MONTHS fro , cause the application to become ABANDON	timely filed  ays will be considered timely.  m the mailing date of this communication.  IED (35 U.S.C. § 133).			
Status						
1)⊠	Responsive to communication(s) filed on 11 A	<u>pril 2005</u> .				
2ạ)⊠	This action is <b>FINAL</b> . 2b) This	action is non-final.				
3)	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
	closed in accordance with the practice under E	Ex parte Quayle, 1935 C.D. 11, 4	453 O.G. 213.			
Dispositi	ion of Claims					
5)□ 6)⊠ 7)□	Claim(s) 1-5,28,29 and 35-37 is/are pending in 4a) Of the above claim(s) is/are withdray Claim(s) is/are allowed.  Claim(s) 1-5,28,29 and 35-37 is/are rejected.  Claim(s) is/are objected to.  Claim(s) are subject to restriction and/o	wn from consideration.				
Applicati	ion Papers					
10)⊠	The specification is objected to by the Examine The drawing(s) filed on 30 April 2001 is/are: a) Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Ex	$\boxtimes$ accepted or b) $\square$ objected to drawing(s) be held in abeyance. So tion is required if the drawing(s) is o	ee 37 CFR 1.85(a). bjected to. See 37 CFR 1.121(d).			
Priority ι	under 35 U.S.C. § 119					
a)(	Acknowledgment is made of a claim for foreign All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority application from the International Bureausee the attached detailed Office action for a list	s have been received. s have been received in Applica rity documents have been received in CPCT Rule 17.2(a)).	ntion No ved in this National Stage			
Attachmen	t(s)					
2) 🔲 Notic 3) 🔲 Infori	re of References Cited (PTO-892) re of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) r No(s)/Mail Date	4) Interview Summar Paper No(s)/Mail I 5) Notice of Informal 6) Other:				

Art Unit: 2857

Page 2

#### **DETAILED ACTION**

# Response to Amendment

The action is responsive to the Amendment filed on 11 April 2005. Claims 1-5,
 28, 29 and 35-37 are pending. Claims 1-5, 28, 29 and 35-37 have been amended.
 Claims 6-27 and 30-34 have been cancelled.

# Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1, 2, 4, 5 and 35-37 are rejected under 35 U.S.C. 103(a) as being unpatentable over Maguire et al. (U.S. Patent No. 6,038,525) (hereinafter Maguire) in view of Robinson et al. (U.S. Patent No. 6,541,783) (hereinafter Robinson).

Referring to claim 1, Maguire teaches a system for controlling a thin film deposition process, comprising: one or more thin film components that deposit a thin film on one or more portions of a wafer (see Maguire, Figure "Begin Deposition of Film"); a thin film deposition component driving system for driving the one or more deposition components (see Maguire, column 3 lines 7-15); a system for directing light on to the deposited thin film and collecting light reflected from the deposited thin film (see Maguire, Figure 8, "Acquire Response Data"); a scatterometry system that detects structural irregularities associated with the deposited thin film by comparing reflected

Art Unit: 2857

light data associated with the deposited thin film with a database comprising known thin film reflecting light signatures (see Maguire, Figure 8, column 4 lines 12-27); and a processor that communicates with the scatterometry system and the thin film deposition component driving system, wherein the processor determines deposition parameter adjustments to the one or more deposition components based at least in part upon data received from the scatterometry system (see Maguire, Figure 8, column 5 lines 61-67), but does not teach that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks.

Robinson teaches that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

It would have been obvious at the time the invention was made to one of ordinary skill in the art to modify Maguire to include the teachings of Robinson because partitioning the mask and determining thickness at the grid blocks would have allowed the skilled artisan to enhance the physical robustness of reticle mask (see Robinson, column 40-44).

Referring to claim 2, Maguire teaches that the scatterometry system captures the light reflected from the thin film (see Maguire, column 3 lines 42-52).

Referring to claim 4, Maguire teaches that the processor determines the deposition parameter adjustments based in part (see Maguire, column a6 lines 1-6) on

Art Unit: 2857

a presence of an unacceptable thin film deposition condition for a portion of the wafer according to the data received from the monitoring system (see Maguire, column 6 lines 13-21), but does not specify that the "portion of the wafer" refers to a "grid block."

Robinson teaches that the processor makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

It would have been obvious at the time the invention was made to one of ordinary skill in the art to modify Maguire to include the teachings of Robinson because determining thickness at the grid blocks would have allowed the skilled artisan to enhance the physical robustness of reticle mask (see Robinson, column 40-44).

Referring to claim 5, Maguire teaches that the deposition parameter adjustments comprise at least one of pressure (see Maguire, column 6 lines 23-31), flow rates of reacting species (see Maguire, column 5 lines 61-67), flow rate of carrier gas (see Maguire, column 6 lines 1-6), and temperature or a combination thereof (see Maguire, column 6 lines 1-6).

Referring to claim 35, Maguire teaches a method for regulating a process for depositing a thin film (see Maguire, column 2 lines 39-48), comprising: using one or more deposition components to deposit a thin film (see Maguire, Figure 8); determining the characteristics of the deposited thin film utilizing reflected light and comparing to known thin film reflected light signatures (see Maguire, Figure 8); and using a processor to coordinate control of the one or more deposition components to deposit subsequent

Art Unit: 2857

thin film based at least in part of the characteristics of the deposited thin data gathered from comparing the reflected light to known thin film light signatures (see Maguire, Figure 8, column 5 lines 61-67), but does not teach that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks.

Robinson teaches that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

It would have been obvious at the time the invention was made to one of ordinary skill in the art to modify Maguire to include the teachings of Robinson because partitioning the mask and determining thickness at the grid blocks would have allowed the skilled artisan to enhance the physical robustness of reticle mask (see Robinson, column 40-44).

Referring to claim 36, Maguire teaches a system for regulating a process for depositing a thin film (see Maguire, column 2 lines 39-48), comprising: means for using one or more deposition components to deposit a thin film (see Maguire, Figure 8); means for determining the acceptability of the thin film deposition utilizing reflected light and comparing to known thin film reflected light signatures (see Maguire, Figure 8); and means for using a processor to coordinate control of the one or more deposition components to deposit the thin film a processor based at least in part of the acceptability of the thin film deposition as determined by comparing the known thin film

Art Unit: 2857

signatures to reflected light (see Maguire, Figure 8, column 5 lines 61-67), but does not teach that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks.

Robinson teaches that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

It would have been obvious at the time the invention was made to one of ordinary skill in the art to modify Maguire to include the teachings of Robinson because partitioning the mask and determining thickness at the grid blocks would have allowed the skilled artisan to enhance the physical robustness of reticle mask (see Robinson, column 40-44).

Referring to claim 37, Maguire teaches a system that control the deposition of a thin film of a wafer (see Maguire, column 2 lines 39-48), comprising: at least one deposition component employed to deposit a thin film of a wafer (see Maguire, Figure 8); a coherent light source directed onto the thin film (see Maguire, column 3 lines 28-41); a receiving component that collects light reflected from the thin film (see Maguire, column 3 lines 42-49); a scatterometry system that analyzes the reflected light to determine one or more properties of the thin film (see Maguire, column 3 lines 46-52); and a processor that controls the at least one deposition component based at least in part on data received from the scatterometry system (see Maguire, Figure 8, column 5 lines 61-67), but does not teach that the processor partitions the mask into a plurality of

Art Unit: 2857

grid blocks and makes a determination of deposition conditions at the one or more grid blocks.

Robinson teaches that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

It would have been obvious at the time the invention was made to one of ordinary skill in the art to modify Maguire to include the teachings of Robinson because partitioning the mask and determining thickness at the grid blocks would have allowed the skilled artisan to enhance the physical robustness of reticle mask (see Robinson, column 40-44).

3. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Maguire et al. (U.S. Patent No. 6,038,525) (hereinafter Maguire) in view of Robinson et al. (U.S. Patent No. 6,541,783) (hereinafter Robinson) and further in view of Moslehi (U.S. Patent No. 5,270,222).

Referring to claim 3, Maguire teaches all the features of the claimed invention except that structural irregularities associated with the thin film include large grains.

Moslehi teaches that structural irregularities associated with the thin film include large grains (see Moslehi, column 14 lines 58-67).

It would have been obvious to one or ordinary skill in the art at the time the invention was made to modify Maguire to include the teachings of Moslehi because

Art Unit: 2857

detecting large grains would have allowed the skilled artisan to generate a diagnosis or prognosis of any fabrication process abnormalities (see Moslehi, column 3 lines 48-57).

4. Claims 28 and 29 are rejected under 35 U.S.C. 103(a) as being unpatentable over Maguire et al. (U.S. Patent No. 6,038,525) (hereinafter Maguire) in view of Gevelber et al. (U.S. Patent No. 6,162,488) (hereinafter Gevelber) and further in view of Robinson et al. (U.S. Patent No. 6,541,783) (hereinafter Robinson).

Referring to claim 28, Maguire teaches a method for monitoring and controlling the deposition of a thin film (see Maguire, column 2 lines 39-48)), comprising: depositing a thin film on a wafer (see Maguire, Figure 8 "Begin Deposition of Film"); directing a light onto the thin film (see Maguire, column 3 lines 28-41); collecting a light reflected from the thin film (see Maguire, column 3 lines 42-49); employing scatterometry means to analyze the reflected light to determine one or more properties of the thin film (see Maguire, column 3 lines 46-52); monitoring structural irregularities associated with the deposited thin film by comparing reflected light data associated with the deposited thin film with a database comprising known thin film reflected light signatures (see Maguire, column 4 lines 12-27); and controlling a deposition component to deposit thin film on the wafer; and using a processor to control the at least one deposition component based at least in part on data received from the scatterometry means (see Maguire, Figure 8, column 5 lines 61-67). Maquire does not teach utilizing a non-linear training system which facilitates determining deposition parameter adjustments according to the properties of the thin film; or that the processor partitions the mask into a plurality of grid

blocks and makes a determination of deposition conditions at the one or more grid blocks.

Gevelber teaches utilizing a non-linear training system which facilitates determining deposition parameter adjustments according to the properties of the thin film (see Gevelber, column 16 lines 2-22 and column 17 lines 56-65).

Robinson teaches that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

It would have been obvious at the time the invention was made to one of ordinary skill in the art to modify Maguire to include the teachings of Gevelber because having a non-linear system would have allowed the skilled artisan to operate the deposition system over a wide range of operating conditions (see Gevelber, column 19 lines 31-36), and further in view of Robinson because partitioning the mask and determining thickness at the grid blocks would have allowed the skilled artisan to enhance the physical robustness of reticle mask (see Robinson, column 40-44).

Referring to claim 29, Maguire teaches that the properties include at least one of thickness (see Maguire, column 6 lines 13-21).

# Response to Arguments

5. Applicant's arguments filed 11 April 2005 have been fully considered but they are not persuasive.

Art Unit: 2857

Applicant argues that Maguire does not teach that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks. However, this limitation is met by Robinson. Robinson teaches that the processor partitions the mask into a plurality of grid blocks and makes a determination of deposition conditions at the one or more grid blocks (see Robinson, column 11 lines 27-50).

### Conclusion

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mary Kate B. Baran whose telephone number is (571) 272-2211. The examiner can normally be reached on Monday - Friday from 9:00 am to 6:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Marc S. Hoff can be reached on (571) 272-2216. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

14 June 2005

